



IRF624STRR Information



For Reference Only

Part Number IRF624STRR
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 250V 4.4A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF624STRR Specifications

Manufacturer Part Number IRF624STRR Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 4.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 14nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.1W (Ta), 50W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB		
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PackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C4.4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs14nC @ 10VInput Capacitance (Ciss) (Max) @ Vds260pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.1W (Ta), 50W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 2.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Category	Discrete Semiconductor Products
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Technology Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 4.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 14nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.1W (Ta), 50W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Series	-
Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C4.4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs14nC @ 10VInput Capacitance (Ciss) (Max) @ Vds260pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.1W (Ta), 50W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 2.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 4.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 14nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.1W (Ta), 50W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case T0-263-3, D2Pak (2 Leads + Tab), TO-263AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ETHET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Interpretature Surplier Device Package Package / Case 10V 4V @ 250μA 4V @ 250μA 14nC @ 10V 260pF @ 25V 260pF @ 25V 260pF @ 25V 270V 27	Drain to Source Voltage (Vdss)	250V
Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 14nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.1W (Ta), 50W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Current - Continuous Drain (Id) @ 25°C	4.4A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 260pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)3.1W (Ta), 50W (Tc)Rds On (Max) @ Id, Vgs1.1 Ohm @ 2.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	14nC @ 10V
FET Feature Power Dissipation (Max) 3.1W (Ta), 50W (Tc) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	260pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 1.1 Ohm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	3.1W (Ta), 50W (Tc)
Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Rds On (Max) @ Id, Vgs	1.1 Ohm @ 2.6A, 10V
Supplier Device Package D2PAK Package / Case D2PAK TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	D2PAK
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

IRF624STRR Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF624STRR Payment Methods





















IRF624STRR Shipping Methods













If you have any question about IRF624STRR, please do not hesitate to contact us!

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